

**Amendments to the Claims:**

This listing of claims replaces all prior versions and listings of claims in the application.

**Listing of Claims:**

1. (Currently Amended): A ferromagnetic p-type single-crystal zinc oxide material consisting essentially of: ~~p-type single-crystal zinc oxide material including~~  
1 to 99 mol% manganese and ,  
a p-type dopant selected from a group consisting of C, N, and oxides thereof, and  
the balance p-type single-crystal zinc oxide,  
wherein said p-type single-crystal zinc oxide material having a hole concentration of  $1 \times 10^{18} \text{ cm}^{-3}$  or more and a low resistance of  $1 \Omega \cdot \text{cm}$  or less.
  
2. (Currently Amended): A ferromagnetic p-type single-crystal zinc oxide material consisting essentially of: ~~p-type single-crystal zinc oxide material including~~  
1 to 99 mol% manganese,  
a p-type dopant selected from a group consisting of C, N, and oxides thereof, and  
an n-type dopant selected from a group consisting of B, Al, In, Ga, Zn, and oxides thereof,  
and  
the balance p-type single-crystal zinc oxide,  
wherein said p-type single-crystal zinc oxide material having a hole concentration of  $1 \times 10^{18} \text{ cm}^{-3}$  or more and a low resistance of  $1 \Omega \cdot \text{cm}$  or less.

3. (Currently Amended): A method for manufacturing a ferromagnetic p-type single-crystal zinc oxide material ~~as defined in claim 1, in which~~ comprising steps of:

holding a semiconductor substrate within a temperature range of 300-800 °C in a vacuum atmosphere of about  $10^{-8}$  Torr;

supplying an atomic gas from a solid-state source of Zn or Zn oxide and an activated oxygen ~~are supplied~~ onto a said semiconductor substrate to grow a single-crystal zinc-oxide thin film on the substrate while an atomic p-type dopant selected from a group consisting of C, N, and oxides thereof and an atomic Mn are supplied all together onto the substrate at a partial pressure of about  $5 \times 10^{-7}$ .

4. (Currently Amended): A method as defined in claim 3 ~~for manufacturing a ferromagnetic p-type single-crystal zinc oxide material including, a p-type dopant, and an n-type dopant, in which~~ , further comprising a step of doping the n-type dopant is doped ~~is doped~~ so as to provide a higher concentration of the p-type dopant than that of the n-type dopant.